

Amendments to the Specification:

Please replace paragraph [0019] with the following amended paragraph:

[0019] Referring now to Figure 1, a first ILD 15 is shown which includes conductors 17 and 18. This ILD is covered with a dielectric layer 13 used as an etching stop and may be fabricated from, for instance, silicon nitride (Si_3N_4) (Si_3N_4). Ideally, the conductors 17 and 18 are fabricated in a low k dielectric to reduce the capacitors between the conductors. Such low k dielectrics are not ideal, however, for capacitors such as the capacitor 14 of Figure 8. The low k dielectrics used for the layer 15 and also for the layer 16 may be a carbon-doped oxide or a polymer based dielectric or other low density dielectrics. As will be seen, this material is not used as the dielectric in the capacitor.

Please replace paragraph [0023] with the following amended paragraph:

[0023] The dielectric layer 20, as mentioned, is preferably a high k dielectric. In one embodiment, silicon nitride is used as the dielectric with a thickness in the range of 30 to 50Å. In another embodiment, a relatively thick silicon nitride layer is used having a thickness of approximately 200Å. Another dielectric that can be used is oxides of titanium, titanium oxide (TiO_x) again, having a thickness of 30 - 50Å. Other high dielectric materials that may be used are tantalum penta oxide (Ta_2O_5) (Ta_2O_5), barrium-stratium-titanate (BST) or lead-zirconium-titanate (PZT). For these higher k materials such as BST, a thicker layer of dielectric may be used, for example 75-150Å of BST.

Please replace paragraph [0024] with the following amended paragraph:

[0024] The conductive barrier layers may be fabricated from typical barrier layer material such as tantalum (T_{α}) (Ta), tantalum nitride ($\text{T}_{\alpha}\text{N}$) (TaN) or a stack comprising tantalum and tantalum nitride.

Please replace paragraph [0025] with the following amended paragraph:

[0025] In some cases, the higher dielectric materials may not be formed on, or compatible with, a tantalum barrier material. For this reason, an electrode layer may be needed between the barrier layer and the dielectric layer. In Figure 2, an electrode layer 25 is shown between the lower barrier layer 19 and the dielectric 20 and a second electrode layer 24 between the upper barrier layer 21 and the dielectric 20. For instance, where BST is used as the dielectric, the electrode material used is ruthenium (R_{α}) (Ru) or iridium (I_{β}) (Ir).